TR	RANSM	Docket No.											
In re A	Under 37 CFR 1.97(b), (c), or (d) In re Application of: Mui, et al.												
	Serial i		October 2		Examiner	Group Art Unit							
Title:					AND REPEATABILITY OF	AN ETCH PROCESS							
Address to: Commissioner for Patents Alexandria, VA 22313-1450													
	37 CFR 1.97(b)												
1. 🛚	The Microbian Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits; or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.												
37 CFR 1.97(c)													
2.	· ,												
	37 CFR 1.97(d)												
3. 🗆	` '												
	Required Statements and/or Fees Under 37 CFR 1.97(c) or (d)												
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		No item of information in the accompanying Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned person, after making reasonable inquiry, no item of information contained in the accompanying Information Disclosure Statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the Information Disclosure Statement. (37 CFR 1.97(e)(2))											
		The fee set forth in 37 CFR 1.17(p). Please credit any overpayment or charge any insufficiencies to deposit account number 20-0782.											
				37 CFR §	§1.704(d)								
4.	foreign	patent office in	n a counterpart appl	nying Informat	tion Disclosure Statement was cite s communication was not received ng of the Information Disclosure Sta	by any individual designated							
		í C	n	Dated:	Lec 12, 2003))							
	Keith P. Taboada, Esq. Certificate of Mailing by First Class Mail												
Reg. No. 45,150 Moser, Patterson & Sheridan, LLP Attorneys at Law 595 Shrewsbury Avenue, Suite 100 Shrewsbury, New Jersey 07702 I certify that this document is being deposited on /2 -/5 ->003 with the U.S. Postal Service as first class mail under 37 CFR §1.8 and is addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 Signature of Person Mailing Correspondence													
732-530-9404 Barbara J. Jackson													
	Typed or Printed Name of Person Mailing Correspondence												

Sheet 1 of 1 sheet(s)

U.S. Depar	tment o	of Commerce, Pate	Docket No.		Serial No.						
(PTO Form			8327/ETCH/SILICON		10/690,318						
•		SCLOSURE STAT	Applicant Mui, et al.		Confirmation No.:						
(Use sever	al shee	ets if necessary)	Filing Date		Group						
		Examiner									
U.S. Paten	t Docu	ıments	SETTE TRAI								
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate				
	A1	2002/0171828	11/21/2002	Cohen et al.	356	328	07/01/2002				
	A2	2002/0072003	06/13/2002	Brill et al.	430	30	10/30/2001				
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	A4	5,926,690	07/20/1999	Toprac et al.	438	17					
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*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation YES NO				
	B1	03/003447	01/09/2003	WIPO	H01L	21/66	\boxtimes				
	B2										
OTHER AF	RT		<u> </u>		-L						
*Examiner Initial	aminer Including Author, Title, Date, Pertinent Pages, Etc.										
C1 Lee, et al., "Analysis of Reflectometry and Ellipsometry Data from Patterned S Characterization and Metrology for UCSI Technology: 1998 International Contest et al., eds., pg 331-335											
	C2	Raymond, "Angle-resolved scatterometry for semiconductor manufacture,", Microlithography World, Winter 2000.									
	C3	Toprac, A., "AMD's Advanced Process Control of Ply-Gate Critical Dimension," Proc. SPIE Vol 3882, pg 62-65, Sept, 1999.									
	C4	s Using a No arch 2002,	ormal Incide	nce							
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		if reference consider						ough			